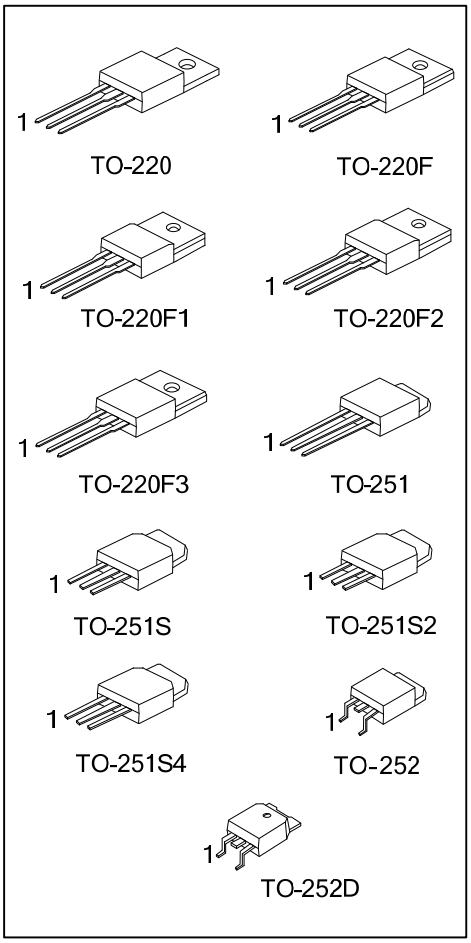
# 4N60K-TA

**Preliminary** ***Power MOSFET***

## 4A, 600V N-CHANNEL POWER MOSFET



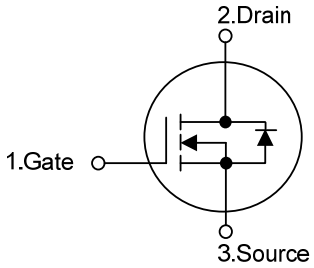

### ■ DESCRIPTION

The UTC **4N60K-TA** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

### ■ FEATURES

* $R_{DS(ON)}$ < 2.8Ω @ $V_{GS}$=10 V, $I_D$=2.0A
* Fast Switching Capability
* Avalanche Energy Specified
* Improved dv/dt Capability, high Ruggedness

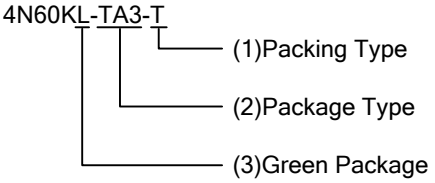
### ■ SYMBOL



## ■ ORDERING INFORMATION

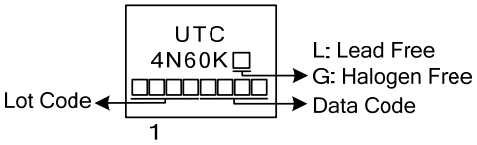
| Ordering Number | | Package | Pin Assignment | | | Packing |
|---|---|---|---|---|---|---|
| Lead Free | Halogen Free | | 1 | 2 | 3 | |
| 4N60KL-TA3-T | 4N60KG-TA3-T | TO-220 | G | D | S | Tube |
| 4N60KL-TF3-T | 4N60KG-TF3-T | TO-220F | G | D | S | Tube |
| 4N60KL-TF1-T | 4N60KG-TF1-T | TO-220F1 | G | D | S | Tube |
| 4N60KL-TF2-T | 4N60KG-TF2-T | TO-220F2 | G | D | S | Tube |
| 4N60KL-TF3T-T | 4N60KG-TF3T-T | TO-220F3 | G | D | S | Tube |
| 4N60KL-TM3-T | 4N60KG-TM3-T | TO-251 | G | D | S | Tube |
| 4N60KL-TMS-T | 4N60KG-TMS-T | TO-251S | G | D | S | Tube |
| 4N60KL-TMS2-T | 4N60KG-TMS2-T | TO-251S2 | G | D | S | Tube |
| 4N60KL-TMS4-T | 4N60KG-TMS4-T | TO-251S4 | G | D | S | Tube |
| 4N60KL-TN3-R | 4N60KG-TN3-R | TO-252 | G | D | S | Tape Reel |
| 4N60KL-TND-R | 4N60KG-TND-R | TO-252D | G | D | S | Tape Reel |

Note: Pin Assignment: G: Gate D: Drain S: Source




(1) T: Tube, R: Tape Reel
(2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TF3T: TO-220F3, TM3: TO-251 TMS: TO-251S, TN3: TO-252, TND: TO-252D
(3) L: Lead Free, G: Halogen Free and Lead Free

## ■ MARKING



## ■ ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25°C, unless otherwise specified)

| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DSS}$ | 600 | V |
| Gate-Source Voltage | | $V_{GSS}$ | ±30 | V |
| Avalanche Current (Note 2) | | $I_{AR}$ | 4.0 | A |
| Drain Current | Continuous | $I_D$ | 4.0 | A |
| | Pulsed (Note 2) | $I_{DM}$ | 16 | A |
| Avalanche Energy | Single Pulsed (Note 3) | $E_{AS}$ | 160 | mJ |
| Peak Diode Recovery dv/dt (Note 4) | | dv/dt | 1.8 | V/ns |
| Power Dissipation | TO-220 | $P_D$ | 106 | W |
| | TO-220F/TO-220F1<br>TO-220F2/TO-220F3 | | 36 | W |
| | TO-251/TO-251S<br>TO-251S2/TO-251S4<br>TO-252/TO-252D | | 50 | W |
| Derate above 25°C | TO-220 | $P_D$ | 0.848 | W/°C |
| | TO-220F/TO-220F1<br>TO-220F2/TO-220F3 | | 0.288 | W/°C |
| | TO-251/TO-251S<br>TO-251S2/TO-251S4<br>TO-252/TO-252D | | 0.4 | W/°C |
| Junction Temperature | | $T_J$ | +150 | °C |
| Operating Temperature | | $T_{OPR}$ | -55 ~ +150 | °C |
| Storage Temperature | | $T_{STG}$ | -55 ~ +150 | °C |

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature
3. L = 20mH, $I_{AS}$ = 4.0A, $V_{DD}$ = 50V, $R_G$ = 25 Ω, Starting $T_J$ = 25°C
4. $I_{SD}$≤4.0A, di/dt ≤200A/μs, $V_{DD}$≤$BV_{DSS}$, Starting $T_J$ = 25°C

## ■ THERMAL DATA

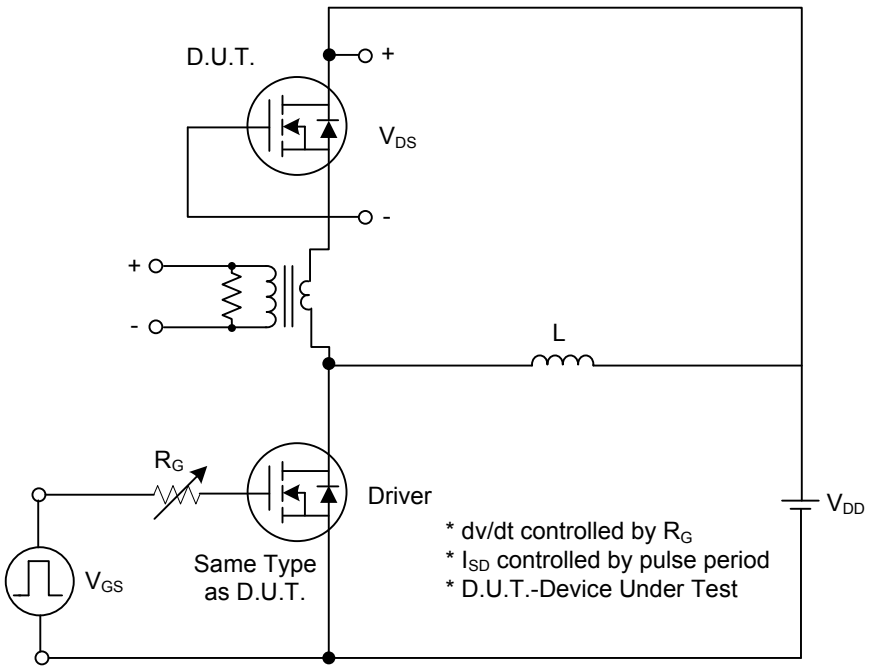
| PARAMETER | | SYMBOL | RATINGS | UNIT |
|---|---|---|---|---|
| Junction to Ambient | TO-220/TO-220F<br>TO-220F1/TO-220F2<br>TO-220F3 | $θ_{JA}$ | 62.5 | °C/W |
| | TO-251/TO-251S<br>TO-251S2/TO-251S4<br>TO-252/TO-252D | | 83 | °C/W |
| Junction to Case | TO-220 | $θ_{JC}$ | 1.18 | °C/W |
| | TO-220F/TO-220F1<br>TO-220F3 | | 3.47 | °C/W |
| | TO-220F2 | | 3.4 | °C/W |
| | TO-251/TO-251S<br>TO-251S2/TO-251S4<br>TO-252/TO-252D | | 2.5 | °C/W |

## ■ ELECTRICAL CHARACTERISTICS ($T_C$ =25°C, unless otherwise specified)

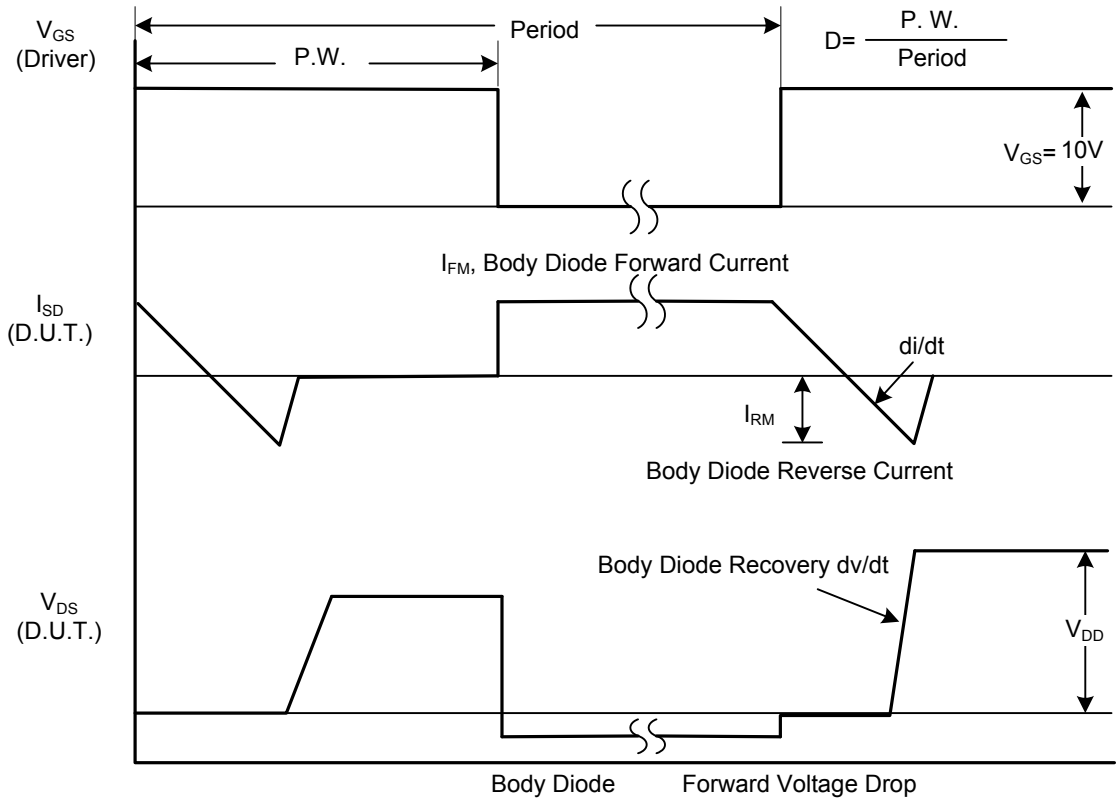
| PARAMETER | | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain-Source Breakdown Voltage | | $BV_{DSS}$ | $V_{GS}$=0V, $I_D$=250μA | 600 | | | V |
| Drain-Source Leakage Current | | $I_{DSS}$ | $V_{DS}$=600V, $V_{GS}$=0V | | | 10 | μA |
| | | | $V_{DS}$=600V, $V_{GS}$=0V, $T_C$=125°C | | | 10 | μA |
| Gate-Source Leakage Current | Forward | $I_{GSS}$ | $V_{GS}$=30V, $V_{DS}$=0V | | | 100 | nA |
| | Reverse | | $V_{GS}$= -30V, $V_{DS}$=0V | | | -100 | nA |
| Breakdown Voltage Temperature Coefficient | | $\triangle BV_{DSS}/\triangle T_J$ | $I_D$=250μA,Referenced to 25°C | | 0.6 | | V/°C |
| **ON CHARACTERISTICS** | | | | | | | |
| Gate Threshold Voltage | | $V_{GS(TH)}$ | $V_{DS}$=$V_{GS}$, $I_D$=250μA | 2.0 | | 4.0 | V |
| Static Drain-Source On-State Resistance | | $R_{DS(ON)}$ | $V_{GS}$=10 V, $I_D$=2.0A | | | 2.8 | Ω |
| **DYNAMIC CHARACTERISTICS** | | | | | | | |
| Input Capacitance | | $C_{ISS}$ | $V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1MHz | | 268 | | pF |
| Output Capacitance | | $C_{OSS}$ | | | 49 | | pF |
| Reverse Transfer Capacitance | | $C_{RSS}$ | | | 5.3 | | pF |
| **SWITCHING CHARACTERISTICS** | | | | | | | |
| Total Gate Charge | | $Q_G$ | $V_{DS}$=50V, $V_{GS}$=10V, $I_D$=13A $I_G$= 100μA (Note1, 2) | | 38 | | nC |
| Gate-Source Charge | | $Q_{GS}$ | | | 4.4 | | nC |
| Gate-Drain Charge | | $Q_{GD}$ | | | 4.6 | | nC |
| Turn-On Delay Time | | $t_{D(ON)}$ | $V_{DS}$=30V, $V_{GS}$=10V, $I_D$=0.5A, $R_G$=25Ω (Note1, 2) | | 50 | | ns |
| Turn-On Rise Time | | $t_R$ | | | 30 | | ns |
| Turn-Off Delay Time | | $t_{D(OFF)}$ | | | 136 | | ns |
| Turn-Off Fall Time | | $t_F$ | | | 30 | | ns |
| **SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS** | | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | | $I_S$ | | | | 4.0 | A |
| Maximum Pulsed Drain-Source Diode Forward Current | | $I_{SM}$ | | | | 16 | A |
| Drain-Source Diode Forward Voltage | | $V_{SD}$ | $V_{GS}$ = 0V, $I_S$ = 4.0A | | | 1.4 | V |
| Reverse Recovery Time | | $t_{rr}$ | $V_{GS}$ = 0V, $I_S$ = 4.0A, $dI_F$ / dt =100A/μs (Note 1) | | 290 | | nS |
| Reverse Recovery Charge | | $Q_{RR}$ | | | 0.23 | | μC |

Notes: 1. Pulse Test: Pulse width≤300μs, Duty cycle≤2%
2. Essentially independent of operating temperature

## ■ TEST CIRCUITS AND WAVEFORMS

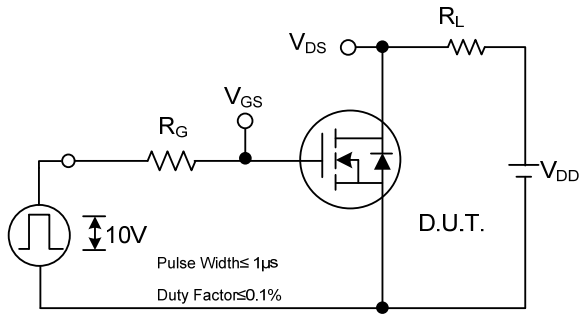



**Peak Diode Recovery dv/dt Test Circuit**

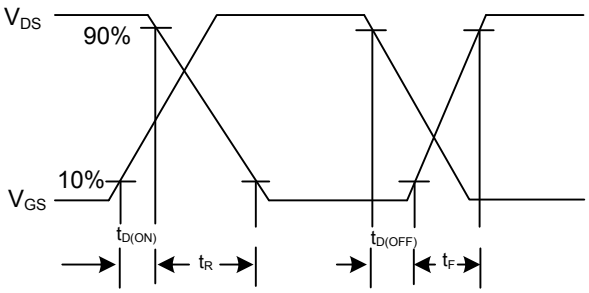



**Peak Diode Recovery dv/dt Waveforms**

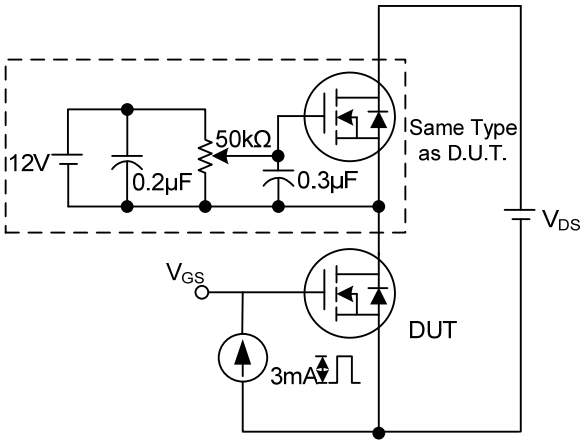
## ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



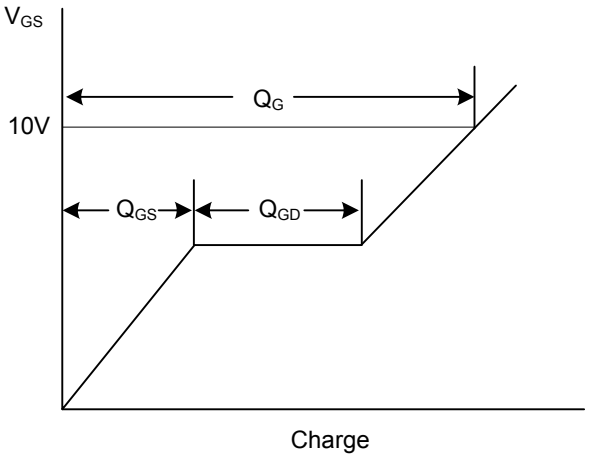

**Switching Test Circuit**



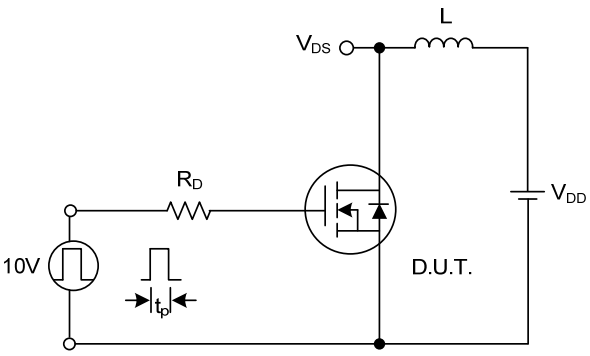

**Switching Waveforms**



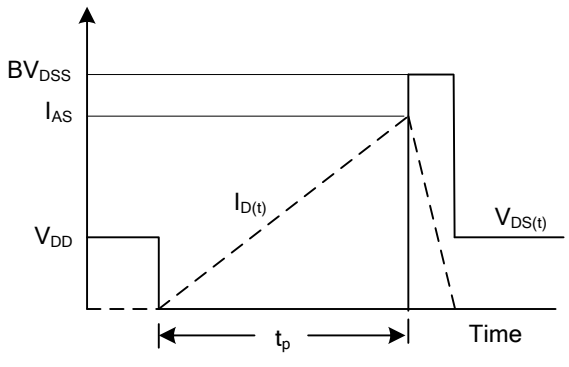

**Gate Charge Test Circuit**




**Gate Charge Waveform**




**Unclamped Inductive Switching Test Circuit**




**Unclamped Inductive Switching Waveforms**